

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	("6388293").PN.	USPAT	OR	OFF	2005/03/24 08:30
L2	1	("4701776").PN.	USPAT	OR	OFF	2005/03/24 08:30
L3	1	("6355524").PN.	USPAT	OR	OFF	2005/03/24 08:30
L4	1	("6518618").PN.	USPAT	OR	OFF	2005/03/24 08:31
L5	1	1 and (nonvolatile or memory or cell or source or drain or region or channel or integrated or circuit or substrate or conductivity or first or second or dope or doping or doped or concentration or overlying or conductive or gate or surface or underlying or opposite or portion or impurity or "0.2" or micro or type-n or type-p or buried or transistor or floating or control or selected or selecte)	USPAT	OR	ON	2005/03/24 09:02
L6	1	"6011725".PN.	USPAT; USOCR	OR	ON	2005/03/24 08:59
L7	1	"5969383".PN.	USPAT; USOCR	OR	ON	2005/03/24 09:00
L8	1	"5768192".PN.	USPAT; USOCR	OR	ON	2005/03/24 09:00
L9	1	"5424979".PN.	USPAT; USOCR	OR	ON	2005/03/24 09:00
L10	1	"5408115".PN.	USPAT; USOCR	OR	ON	2005/03/24 09:01
L11	1	10 and (nonvolatile or memory or cell or source or drain or region or channel or integrated or circuit or substrate or conductivity or first or second or dope or doping or doped or concentration or overlying or conductive or gate or surface or underlying or opposite or portion or impurity or "0.2" or micro or type-n or type-p or buried or transistor or floating or control or selected or selecte)	USPAT	OR	ON	2005/03/24 09:06

L12	1	2 and (nonvolatile or memory or cell or source or drain or region or channel or integrated or circuit or substrate or conductivity or first or second or dope or doping or doped or concentration or overlying or conductive or gate or surface or underlying or opposite or portion or impurity or "0.2" or micro or type-n or type-p or buried or transistor or floating or control or selected or selecte)	USPAT	OR	ON	2005/03/24 09:08
L13	714	438/201	USPAT	OR	ON	2005/03/24 09:08
L14	514	438/211	USPAT	OR	ON	2005/03/24 09:08
L15	956	438/259	USPAT	OR	ON	2005/03/24 09:09
L16	863	438/266	USPAT	OR	ON	2005/03/24 09:09
L17	2594	438/257	USPAT	OR	ON	2005/03/24 09:10
L18	605	438/263	USPAT	OR	ON	2005/03/24 09:10
L19	1453	438/264	USPAT	OR	ON	2005/03/24 09:10
L20	412	438/311	USPAT	OR	ON	2005/03/24 09:11
L21	2290	438/238	USPAT	OR	ON	2005/03/24 09:11
L22	1251	438/381	USPAT	OR	ON	2005/03/24 09:11
L23	1561	438/585	USPAT	OR	ON	2005/03/24 09:12
L24	758	438/593	USPAT	OR	ON	2005/03/24 09:12
S42 8	4	10/266378	USPAT	OR	ON	2005/03/23 17:37
S42 9	4	10/262785	USPAT	OR	ON	2005/03/23 17:38
S43 0	1	("6355524").PN.	USPAT	OR	OFF	2005/03/23 17:50
S43 1	1	("6518618").PN.	USPAT	OR	OFF	2005/03/23 18:02
S43 2	2	10/393212	USPAT	OR	ON	2005/03/23 18:25
S43 3	74	(nonvolatile adj memory adj cell) and source and drain and channel and region and (first adj conductivity) and (second adj conductivity) and n-type and p-type and floating and gate and concentration	USPAT	OR	ON	2005/03/23 18:28

S43 4	0	(nonvolatile adj memory adj cell) and source and drain and channel and region and (first adj conductivity) and (second adj conductivity) and n-type and p-type and floating and gate and concentration and (conductive adj gate) and (buried adj channel adj transistor)	USPAT	OR	ON	2005/03/23 18:29
S43 5	0	(nonvolatile adj memory adj cell) and source and drain and channel and region and (first adj conductivity) and (second adj conductivity) and n-type and p-type and floating and gate and concentration and (buried adj channel adj transistor)	USPAT	OR	ON	2005/03/23 18:29
S43 6	2	(nonvolatile adj memory adj cell) and source and drain and channel and region and (first adj conductivity) and (second adj conductivity) and n-type and p-type and floating and gate and concentration and (conductive adj gate)	USPAT	OR	ON	2005/03/24 08:30